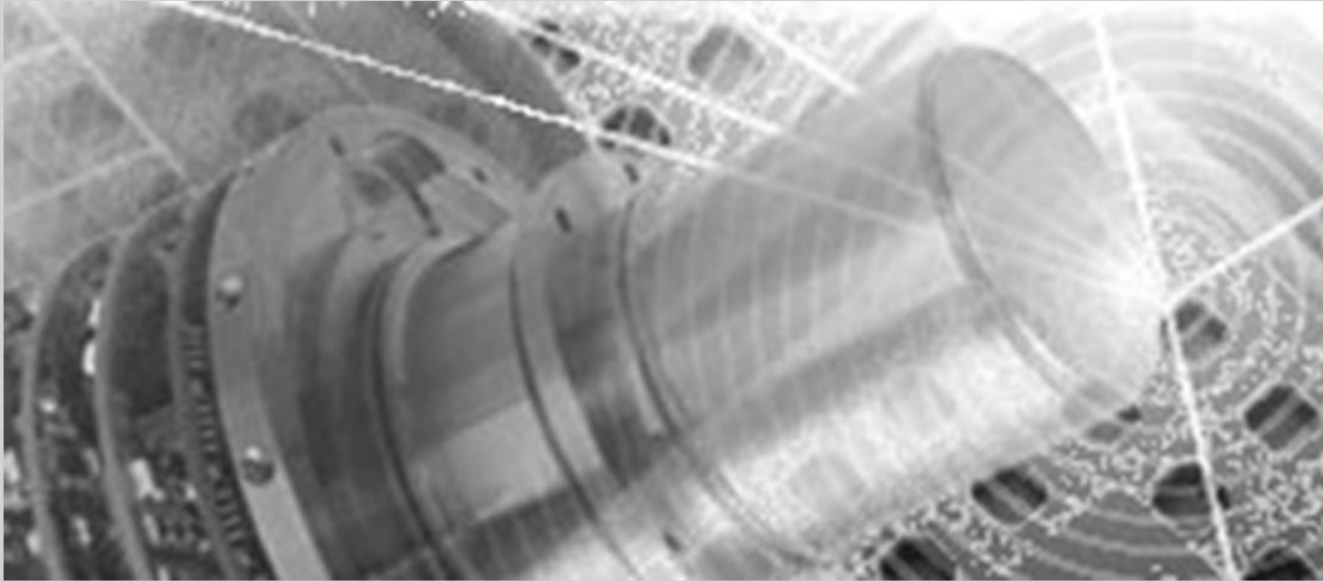


AIM INFRAROT-MODULE GmbH



Next generation IR technology for imaging applications
Rainer Breiter, Heinrich Figgemeier, Ingo Ruehlich

9th NATO Military Sensing Symposium
SENSORS & ELECTRONICS TECHNOLOGY (SET) PANEL
SET-241, Quebec City, Canada

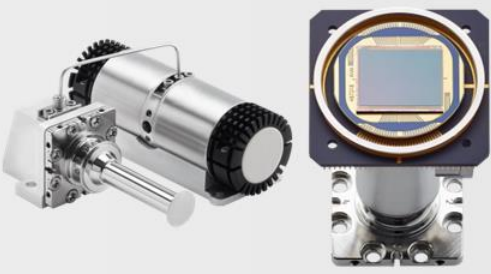
■ OUTLINE

- **Introduction: IR technology development at AIM**
- **Multi-Color IR detectors**
- **Reduction of Size, Weight and Power (SWaP)**
- **SWIR Imaging**
- **Summary**

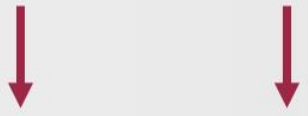
INTRODUCTION

IR technology at AIM

SWIR to VLWIR

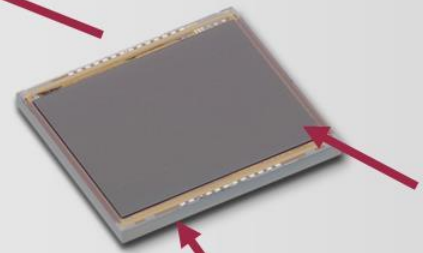
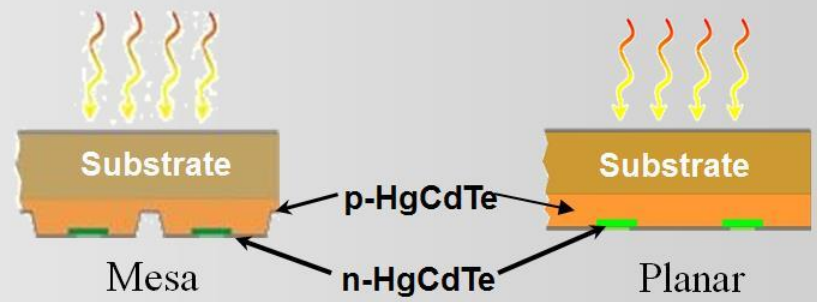


Cooler Dewar

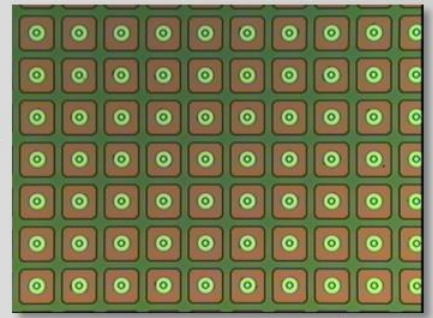


Integrated Detector Cooler Assembly

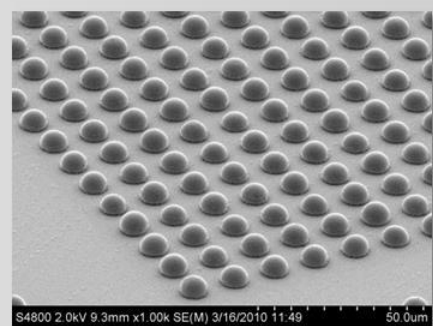
- Optical Interface
- Cooler Integration
- Proximity Electronics



FPA



Array



ROIC



- Epitaxy:
LPE grown MCT on CZT
or
MBE grown MCT on GaAs
- Planar / Mesa process

40µm → 10µm Pitch
7.5µm ⌚

- Reflow process
- Flip-chip by soldering

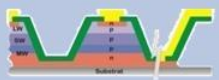
180nm Si CMOS

INTRODUCTION

IR technology development at AIM: MCT based IR detectors

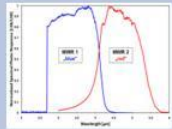
Next GEN

Dual-Band MWIR/LWIR



640x512 (✓)
1280x720 ⌚

Dual-Color MWIR/MWIR



320x256 ⌚
Temporal & Spatial
Coincidence

High-Definition (MCT)

1280x1024 ✓ 1024x768 ✓
1280x720 ✓



MWIR/MWIR
Focal Plane Array Results

Low SWaP

(Reduce Size, Weight and Power)

MWIR Detector Operating Temperature (HOT)

95K → 140K ✓ → 160K ✓ → 180K ⌚

Smaller Cooler

15W → 3W ✓ → < 2W ✓



Smaller Pixel

24μm → 15μm ✓ → 12μm ✓ → 10μm ✓
↓ ⌚
7.5μm



Compact, high resolution
MWIR Engine

SWIR

Shortwave Infrared

Hyperspectral Imaging

384x288 ✓
1024x256 ✓



eSWIR for Enhanced Vision

640x512 15μm ✓
640x512 10μm ⌚

Gated-Viewing (active)

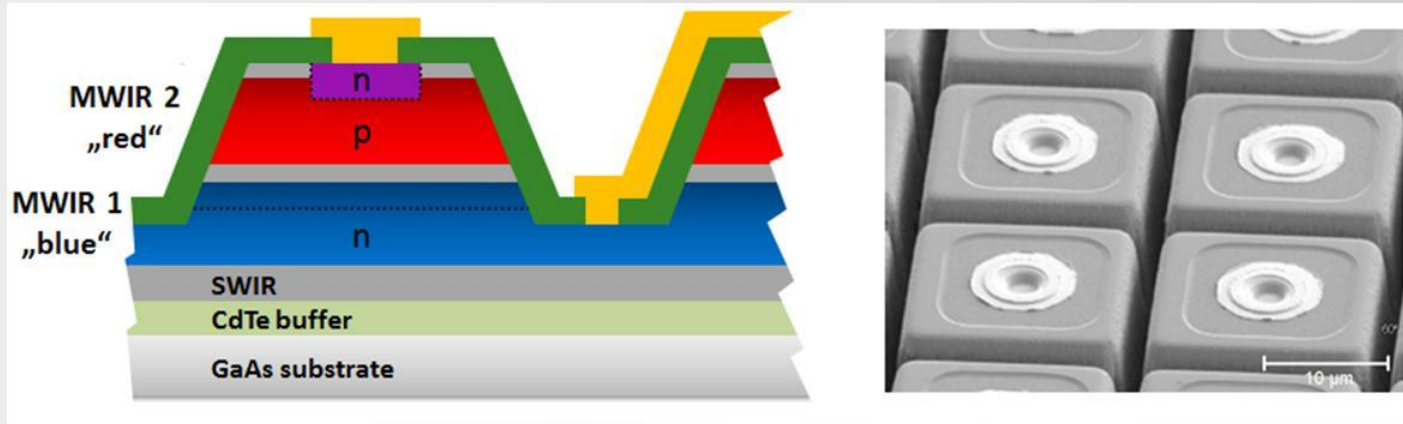
640x512 15μm (✓)



eSWIR (0.9μm – 2.5μm) Imaging
for Enhanced Vision
SWIR Modules for Active Imaging
with Gated Viewing

■ MULTI-COLOR IR DETECTORS

MBE MCT on GaAs: MWIR/MWIR Focal Plane Array results



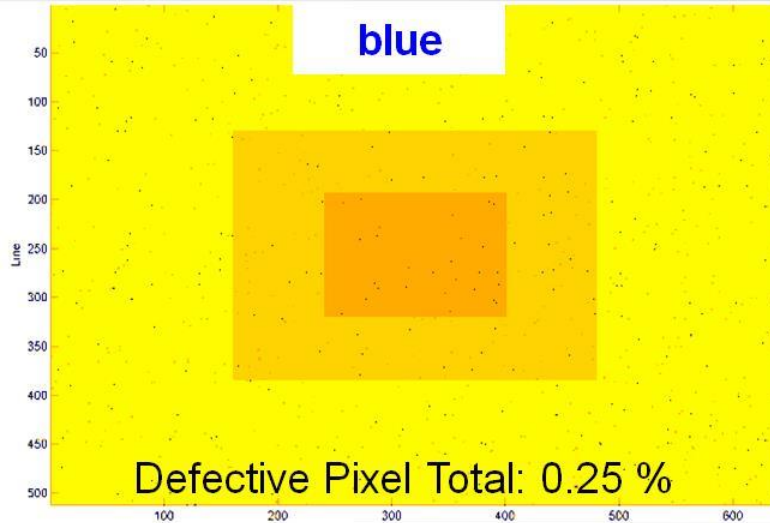
- Design 640 x 512 pixel 20 μm pitch
- Backside-illuminated back-to-back diodes
- Mesa structure with one electrical contact per pixel
- MWIR 1 region doped with In during MBE growth
- P-N junction in MWIR 2 formed by Boron implantation
- Integration in Testdewar and operation with linear stirling cooler
- Cold shield F/2

MULTI-COLOR IR DETECTORS

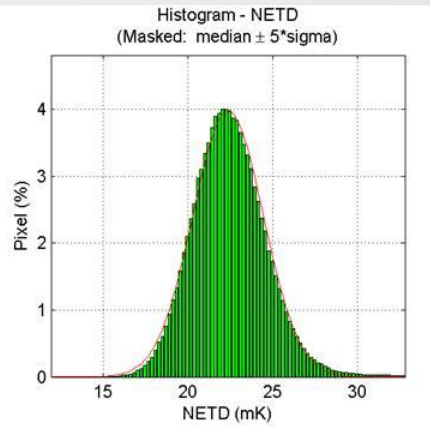
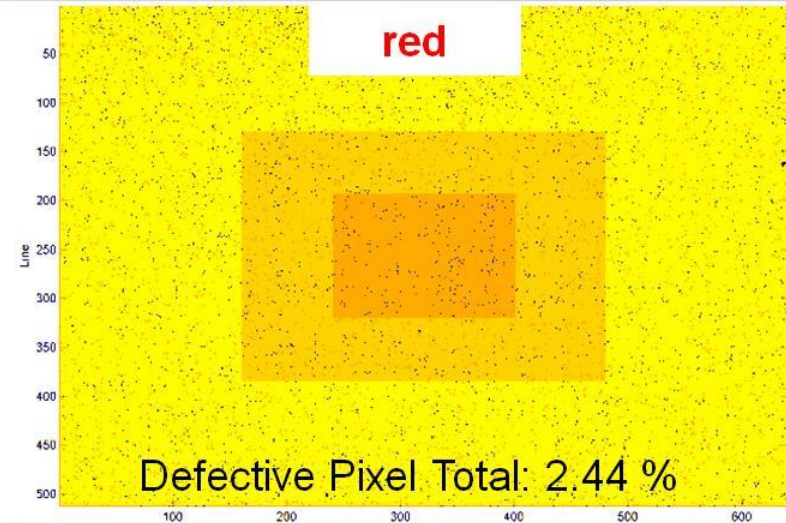
MBE MCT on GaAs: MWIR/MWIR Focal Plane Array results

NETD and defective pixel evaluation, Top=80K

tint= 4 ms

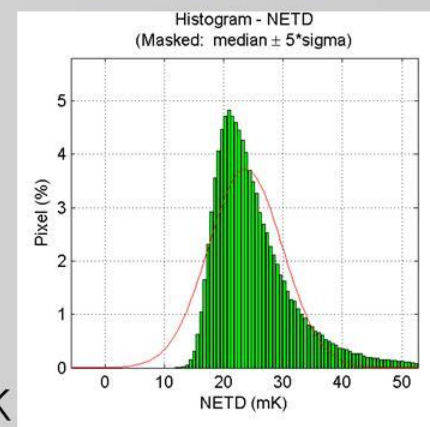


tint= 1 ms



NETD@300K= 22.5mK

Defective criteria:
 Gain $\leftrightarrow [0.5, 2] * \text{mean}$
 NETD $\leftrightarrow [0, 2] * \text{mean}$
 Noise $\leftrightarrow [0, 5] * \text{median}$

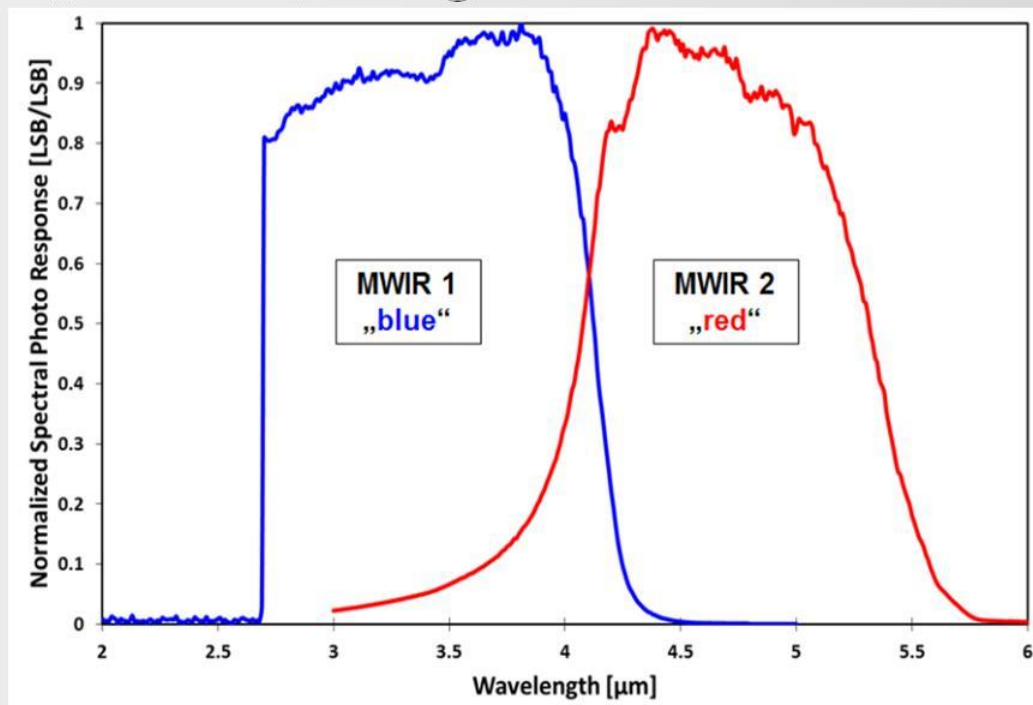


NETD@300K= 25.0mK

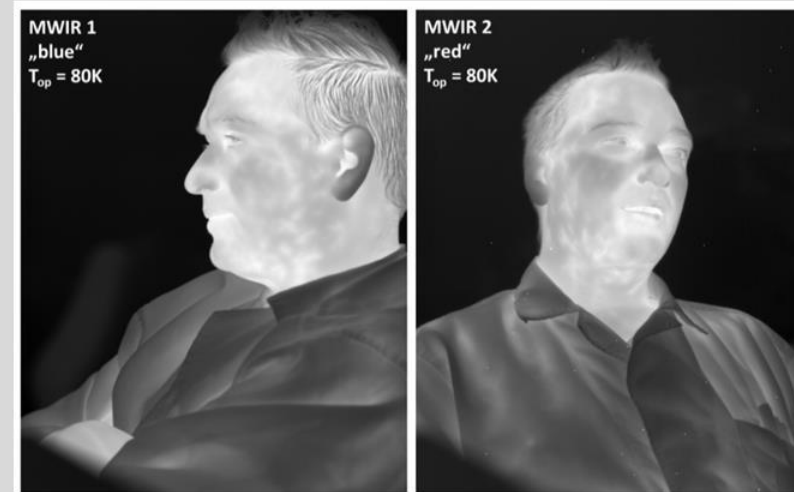
■ MULTI-COLOR IR DETECTORS

MBE MCT on GaAs: MWIR/MWIR Focal Plane Array results

Spectral Response @ 80K



Images @ 80K



blue: cut-off 4.13μm (50%)
red: cut-off 5.32μm (50%)

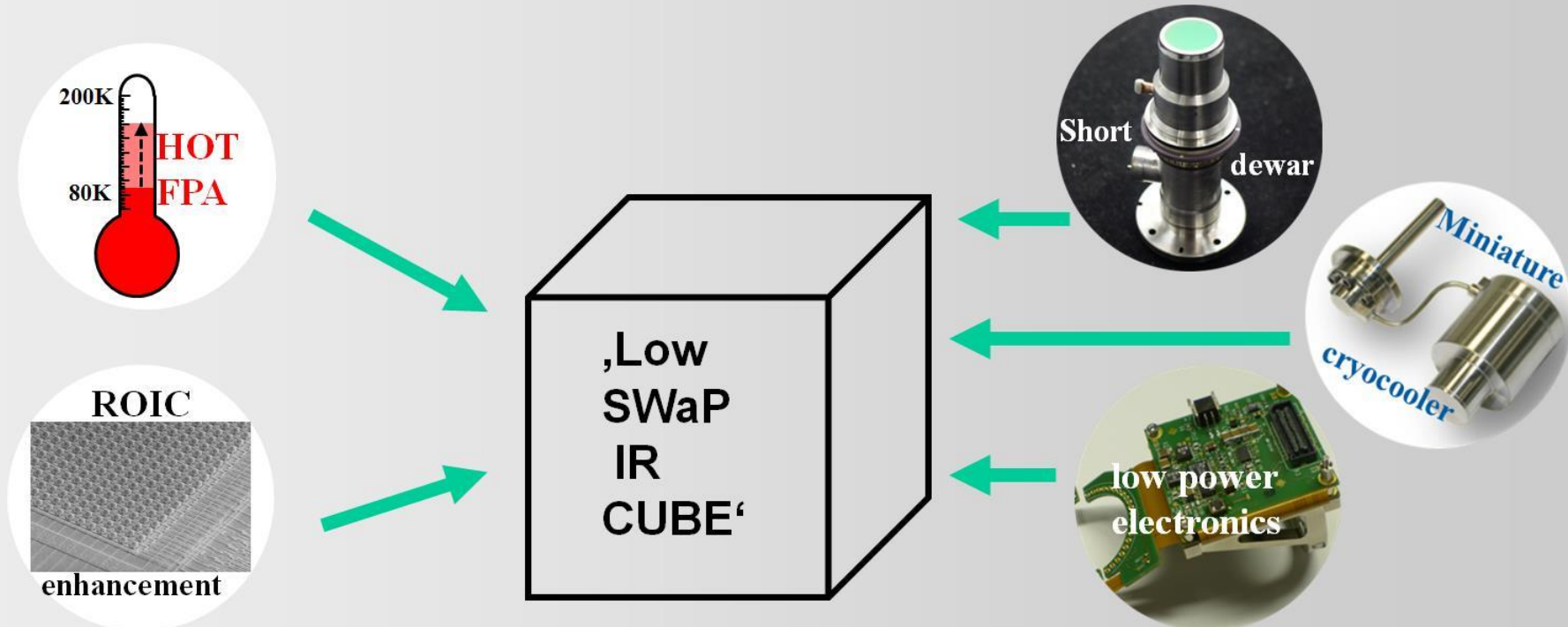
- MCT MBE MWIR/MWIR layers on GaAs successfully grown
- Low spectral crosstalk and QE >60% for blue and red color
- Design 320x256 in 30μm pitch with temporal and spatial coincidence in development

■ REDUCTION OF SIZE, WEIGHT AND POWER (SWAP)

Motivation: IR detector solution for ...

- Applications with limited space, critical thermal management like small gimbals
- Handheld soldier thermal sights for observation and targeting
- Or any other application that requires low SWaP characteristics

⇒ Desire for high-performance IR-solutions in a small package



■ REDUCTION OF SIZE, WEIGHT AND POWER (SWAP)

HOT 1024x768, 10 μ m pitch FPA

Key design goals FPA

- HOT ~160K aimed
- High spatial resolution
- Small pixel pitch
- Preserve ~5 μ m cutoff wavelength

Challenges

- Reduction of dark current
- Preserve high e/o-performance
- High quantum efficiency
- In-bump technology / hybridization

Realization

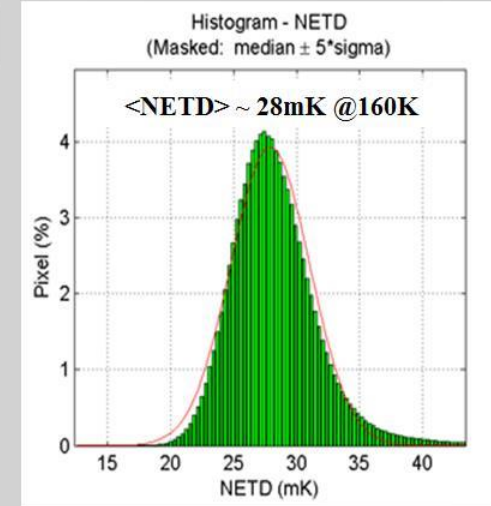
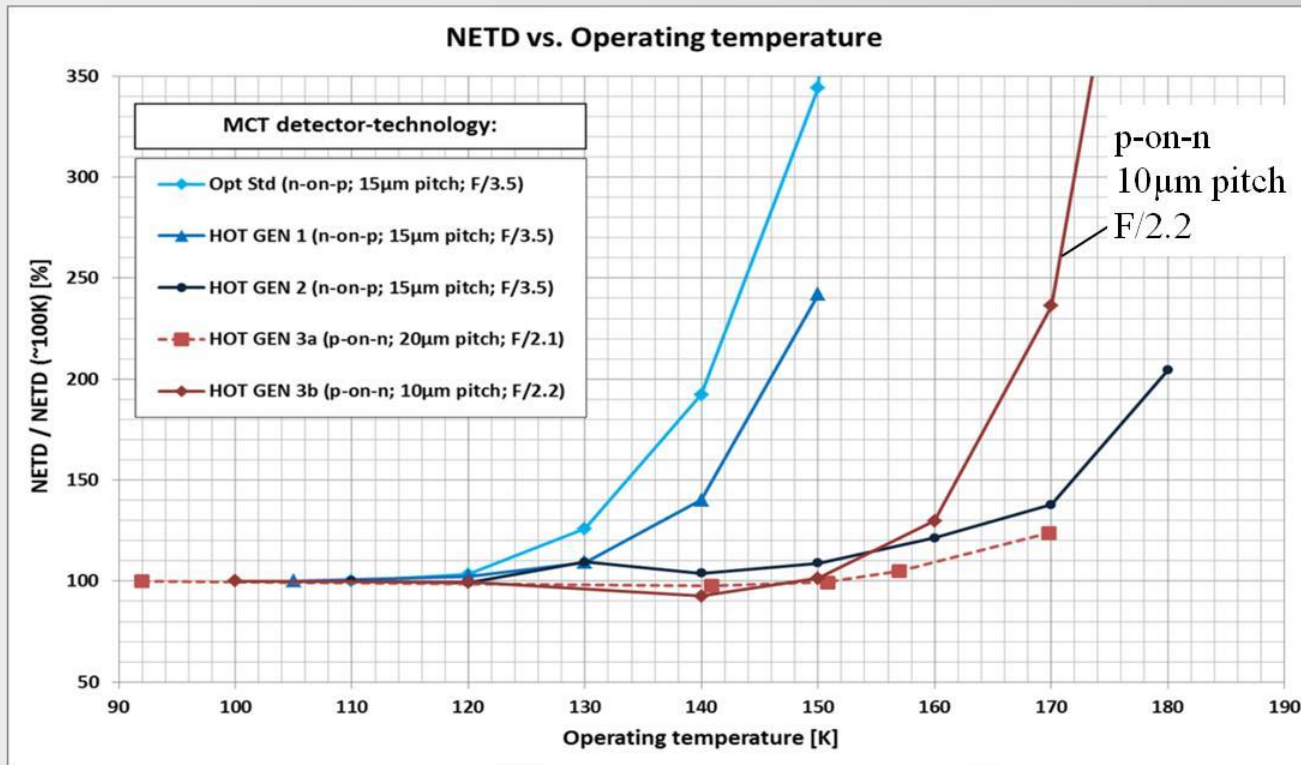
- Decision for 1024x768, 10 μ m format
- Planar p-on-n detector technology

REDUCTION OF SIZE, WEIGHT AND POWER (SWAP)

HOT FPAs, performance

HOT 1024x768, 10 μ m pitch FPA

<NETD> @300K, Integration time adjusted for ~50% well fill, $\lambda_{\text{cutoff}} \sim 5.2 \pm 0.1 \mu\text{m}$ @80K



IR image @160K

(2-point NUC and BPR applied)

- Promising first p-on-n results in 10 μ m pixel pitch
- Further potential by optimizing passivation and doping level
- Limitation for HOT \geq 160K is explained by consequences from rising dark current rather than from defective pixel level

■ REDUCTION OF SIZE, WEIGHT AND POWER (SWAP)

Additional key components

Low Power ROIC

- Usage of 4 analog video outputs with optimized amplifiers
- Usage of internal DACs and current sources
- Set ,nice to have'-features aside, focus on essential features

Short Dewar

- Usage of short 5mm coldfinger with wall thickness $< 100\mu\text{m}$
- Reduced heat load contribution of bond wires
- F/2.2 standard configuration
- Number of single parts is kept low \rightarrow cost-efficient

Small, low power Microcooler

- Gap between rotary integral and split linear coolers in terms of power consumption is closing at HOT
- HOT linear cryocoolers have advantages of high lifetimes, low audible noise, low vibrational output



Total length $\sim 47\text{mm}$
Weight only $\sim 42\text{g}$



SX020 with 5mm micro CF
 $\sim 2W_{AC}$ @160K

Compact, high resolution MWIR Engine

Design

- Detector-dewar assembly and cryocooler in parallel configuration
- Command&Control electronics and cooler drive electronics combined to on one printed board
- All subcomponents mounted on a common frame
- Mounting interfaces for assembling of IR-engine on system level and for installing of optics

Characteristics

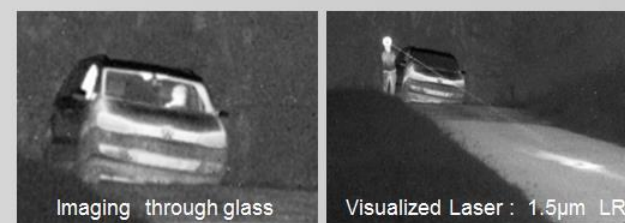
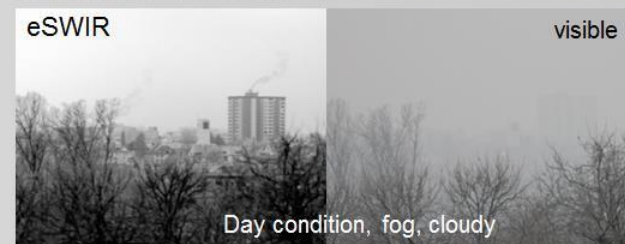
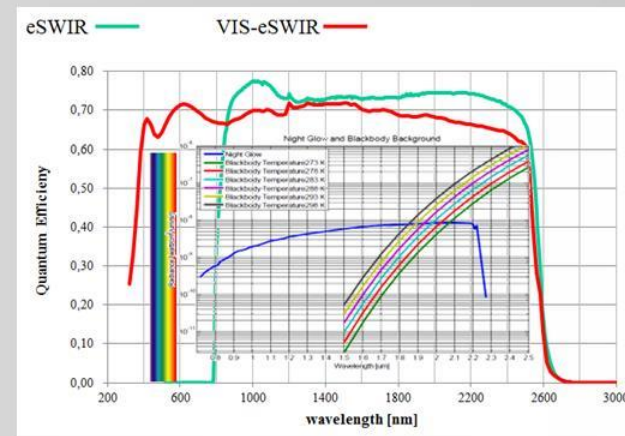
- Small form factor (length x height x width):
60mm x 60mm x 50mm (2.36 x 2.36 x 1.97 inches)
 - Light weight: ~0.37kg (~0.8lbs)
 - Only one system interface connector
 - Cool down time ~3min @ +23°C (Top ~160K)
 - Total input power only ~3.6W @160K (Basic functions)
- Differences in SWaP characteristics compared to uncooled IR-modules are getting small



SWIR IMAGING

eSWIR (extended SWIR) for Enhanced Vision

- MCT eSWIR Modules: 640x512
 - 15µm pitch
 - 10µm pitch (Low SWaP-C)
- Spectral response 0.9µm – 2.5µm (VIS option 0.4µm – 2.5µm)
- Combining reflective + thermal imaging in one sensor
- Full coverage of the nightglow spectrum
- Thermal target radiation in complete darkness
- „Out-of-band“ operation >2µm, not detectable with InGaAs



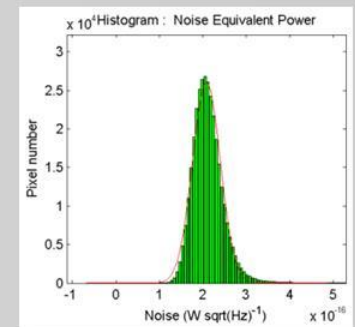
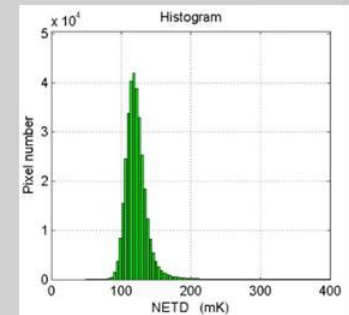
■ SWIR IMAGING

eSWIR 640x512 FPAs in 15 μ m and 10 μ m Pitch

- MCT by Liquid-Phase-Epitaxy (LPE) on CdZnTe substrates (lattice-matched), n-on-p polarity
- Spectral range 0.9 μ m – 2.5 μ m
- Top \geq 175K
- **640x512 15 μ m pitch \Rightarrow Integrated to Field Demonstrator Camera**
 - QE 74% (average between 1 μ m and 2.4 μ m)
 - Dark current 1nA/cm² @ Top \sim 175K
 - Low Noise ROIC
 - 2 Gains: High Gain 125,000e-, Low Gain 1.800.000e-
 - ITR and IWR Snapshot, RS with CDS option
 - Selectable operation parameters from day condition (low gain, tint=48 μ s) to full darkness (high gain, tint=38.6ms)
 - IDCA with Microcooler and F/2 cold shield
- **640x512 10 μ m pitch \Rightarrow only 44% of the array size with 15 μ m pitch**
- MCT by Molecular-Beam-Epitaxy (MBE) on 4" GaAs substrates in development, currently an order of magnitude higher dark current at 175K

640x512 15 μ m
 Top = 180K
 RS with CDS, High Gain
 tint=38.6ms

NETD@300K:
 \langle NETD $\rangle \sim 119$ mK



NEP:
 \langle NEP $\rangle \sim 2.1 \times 10^{-16}$ W/Hz^{1/2}

■ SWIR IMAGING

Comparison of different sensor technologies (eSWIR 640x512 15 μ m pitch)

Field trials outside urban area, objects in 100m distance, forest in the background

A) Overcast night

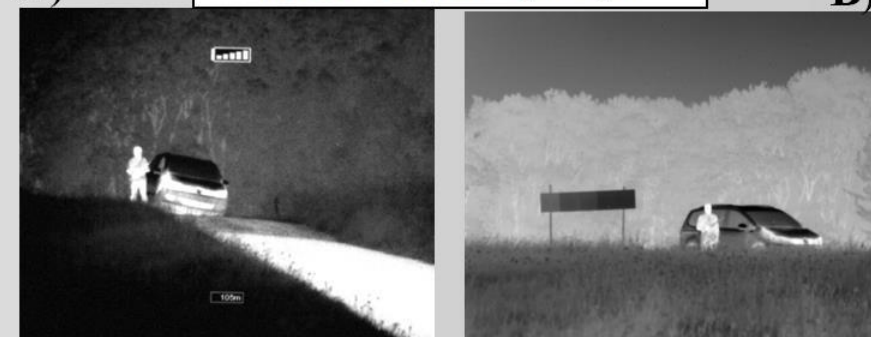
B) No clouds, almost full moon

A) eSWIR 0.9 μ m – 2.5 μ m **B)**



AIM eSWIR Sight, FOV 6°x4.9°, NETD@300K ~150mK

A) MWIR Thermal 3.4 μ m - 5 μ m **B)**



AIM HuntIR Mk2, FOV 6°x4.9°, NETD@300K ~30mK

A) SWIR 0.9 μ m – 1.8 μ m **B)**



AIM SWIR Sight, FOV 6°x4.9°

A) Image Intensifier recorded with camera, 0.4 μ m – 0.9 μ m **B)**

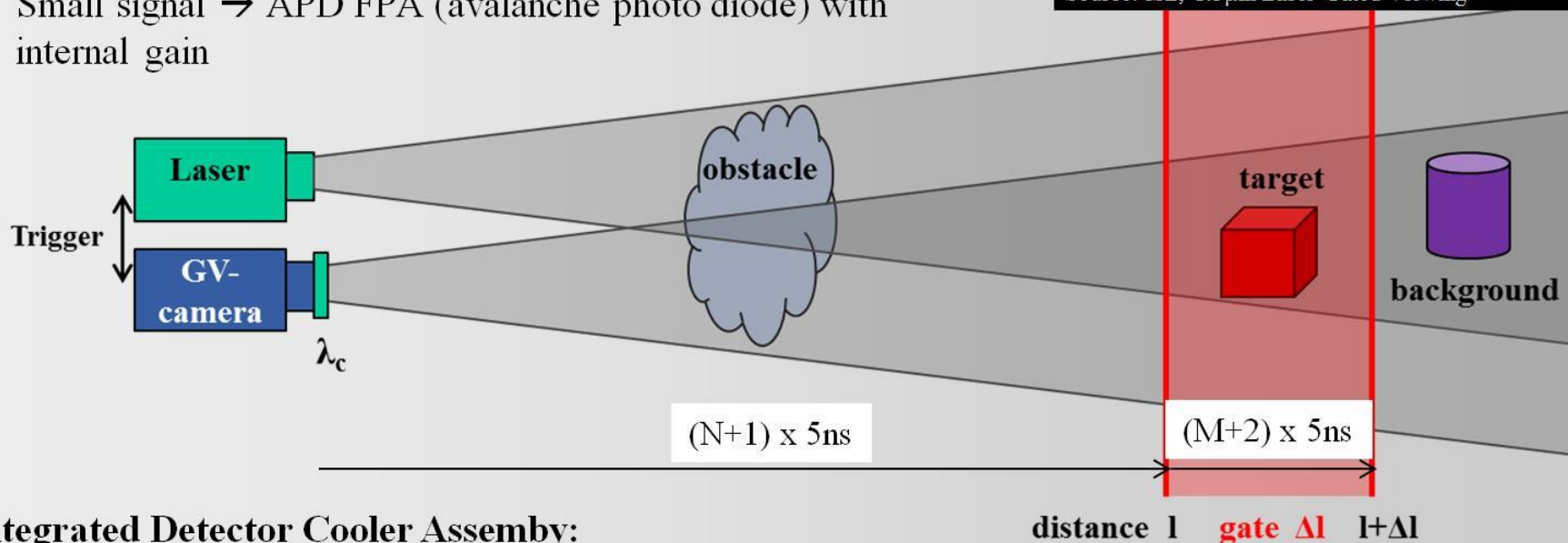


Hensoldt NSV600, Gen2 I², FOV 8°

SWIR IMAGING

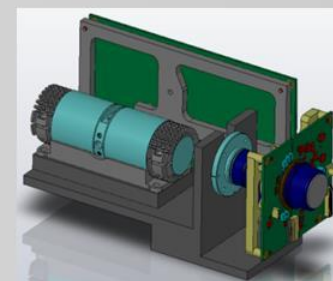
2D MCT SWIR Module for Gated Viewing

- Pulsed laser illuminator 1.5 μm
- Fast-gating camera \rightarrow ROIC with on-chip gating functionality
- Small signal \rightarrow APD FPA (avalanche photo diode) with internal gain



Integrated Detector Cooler Assembly:

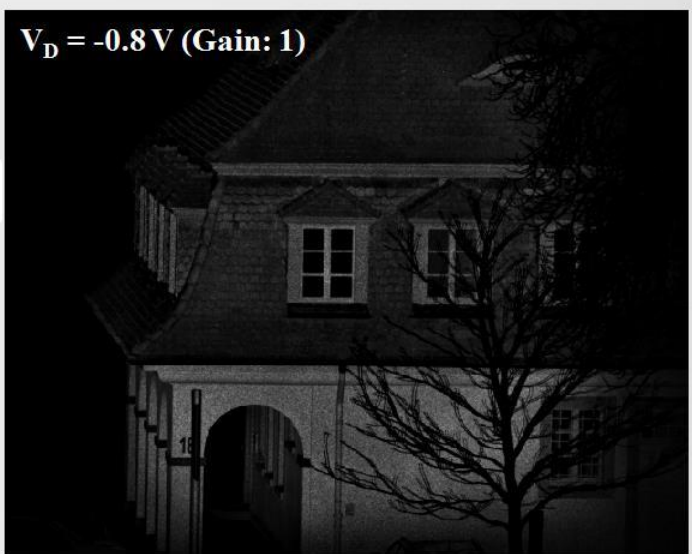
- Detector MCT n-on-p APD, 640x512 15 μm , cut-off 2.5 μm
- ROIC with internal PLL 200 MHz (5ns), operated by master clock
- Full frame rate max. 100Hz
- Programmable gate delay N and gate integration M in steps of 5ns
- Snapshot imaging mode, integrate then read



SWIR IMAGING

SWIR GV imaging results

100 m

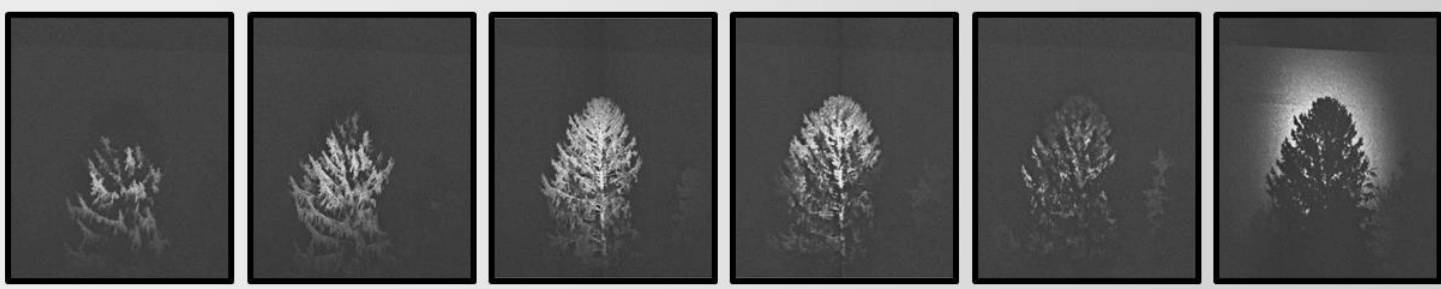


MCTAPD
Gain 1 \Rightarrow 2.3

$E_{\text{LASER}} = 50 \text{ mJ}$
 $\lambda_{\text{LASER}} = 1.5 \mu\text{m}$

Source: Benjamin Göhler, Peter Lutzmann, Simon Brunner, H. Bürsing, Fraunhofer IOSB, Ettlingen, Germany

Receiver optics $f=90\text{mm}$, $F/2$



228m

Range

315m

Gating Function

$E_{\text{LASER}} = 8\text{mJ}$
 $\sim 5\text{ns}$ pulse duration
 $\lambda_{\text{LASER}} = 1.57 \mu\text{m}$
Gate time = 15ns
($\approx 2.3\text{m}$ range gate)
Gain = 1

- **IR technology development at AIM**
 - MCT based IR technology from SWIR to VLWIR including Multi-Color Arrays
- **Multi-Color IR detectors**
 - MWIR/MWIR MBE grown MCT on GaAs demonstrated
 - Final MWIR/MWIR design with spatial & temporal coincidence
- **Reduction of Size, Weight and Power (SWaP)**
 - Compact, high resolution MWIR Engine
 - Key component HOT FPA with Top=160K, 1024x768 10 μ m pitch
 - Low power ROIC, short Dewar, split linear Microcooler, low power electronics
- **SWIR Imaging**
 - eSWIR combining reflective + thermal imaging for Enhanced Vision
 - 2D SWIR Module for Active Imaging with Gated Viewing capability

■ ACKNOWLEDGEMENTS

The development activities presented here in were partially supported by the German MOD under different BAAINBw contracts.

This support is gratefully acknowledged.

THANK YOU FOR YOUR ATTENTION